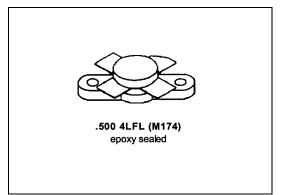
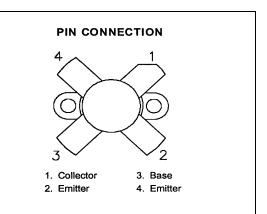


RF & MICROWAVE TRANSISTORS HF SSB APLICATIONS

Features

- 30 MHz
- 12.5 VOLTS
- P_{OUT} = 100 WATTS
- G_{PE} = 12.0 dB MINIMUM
- IMD = -30 dBc
- GOLD METALLIZATION
- COMMON EMITTER CONFIGURATION





DESCRIPTION:

The MS1051 is a 12.5 V Class C epitaxial silicon NPN planar transistor designed primarily for HF communications. This device utilizes state-of-the-art diffused emitter ballasting to achieve extreme ruggedness under severe operating conditions.

ABSOLUTE MAXIMUM RATINGS (Tcase = 25^{\circ}C)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	36	V
V _{CEO}	Collector-Emitter Voltage	18	V
V _{EBO}	Emitter-Base Voltage	4.0	V
I _C	Device Current	20	Α
P _{DISS}	Power Dissipation	290	W
TJ	Junction Temperature	+200	°C
T _{STG}	Storage TEmperature	-65 to +150	°C

THERMAL DATA

R _{TH(J-C)} Thermal R	esistance Junction-case	0.6	°C/W
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Revision B, January 2010

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ELECTRICAL SPECIFICATIONS (Tcase = 25^{\circ}C)

STATIC

Symbol	Test Conditions	Value			Unit	
Symbol		Test conditions	Min.	Тур.	Max.	Onit
BV _{CBO}	I _C = 100mA	I _E = 0mA	36			V
BV _{CES}	I _C = 100mA	$V_{BE} = 0V$	36			V
BV _{CEO}	I _c = 100mA	I _B = 0mA	18			V
BV _{EBO}	I _E = 20mA	I _C = 0mA	4.0			V
I _{CES}	V _{CE} = 15V	I _c = 0mA			20	mA
h _{FE}	$V_{CE} = 5V$	I _c = 5mA	10		200	

DYNAMIC

Symbol	Test Conditions		Value			Unit	
Symbol			Min.	Тур.	Max.	Onit	
POUT	f = 30 MHz	V _{CE} = 12.5 V	I _{CQ} = 150mA	100			w
G _P	f = 30 MHz	V _{CE} = 12.5 V	I _{CQ} = 150mA	11	13		dB
IMD ₃ *	P _{OUT} = 100 W PEP	V _{CE} = 12.5 V	I _{CQ} = 150mA			-30	dBc
C _{OB}	f = 1 MHz	V _{CB} = 12.5 V			400		pf

Conditions: f1 = 30.000MHz f2 = 30.001MHz

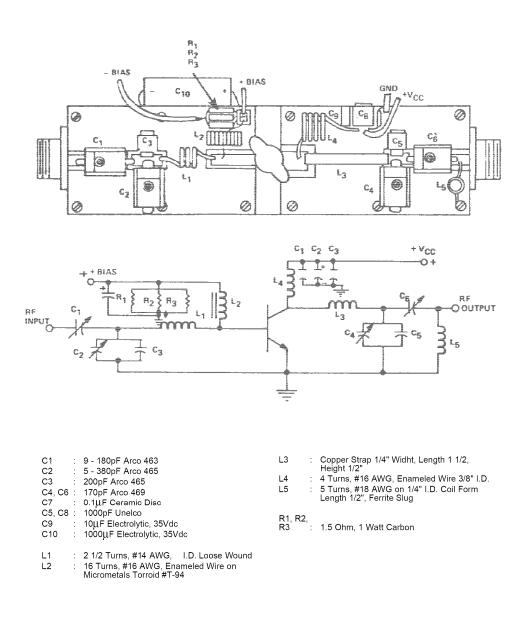


IMPEDANCE DATA

FREQ	$Z_{IN}(\Omega)$	$Z_{CL}(\Omega)$		
30 MHz	0.57 + j 0.78	0.80 + j 0.43		

 P_{OUT} = 100 WPEP, V_{CE} = 12.5 V

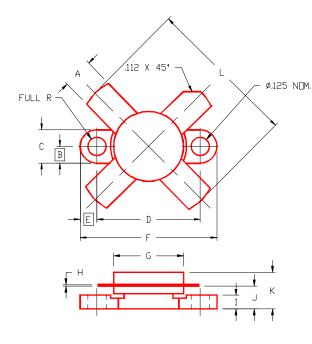
TEST CIRCUIT



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PACKAGE MECHANICAL DATA



PACKAGE STYLE M174

	MINIMUM	MAXIMUM		MINIMUM	MAXIMUM
	INCHES/MM	INCHES/MM		INCHES/MM	INCHES/MM
A	.220/5,59	.230/5,84	Ι	.090/2,29	.110/2,79
В	.125/	′3,18	J	.160/4,06	.175/4,45
С	.245/6,22	,255/6,48	К		.280/7,11
D	.720/18,28	.730/18,54	L		1.050/26,67
E	,125/3,18				
F	.970/24,64	.980/24,89			
G	.495/12,57	.505/12,83			
Н	,003/0,08	.007/0,18			